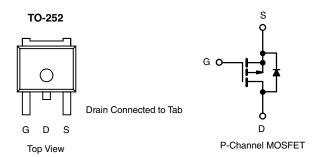


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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0094			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0160			
I <sub>D</sub> (A)	- 90			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>q</sub> and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD90P04-9m4L-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 40		
Gate-Source Voltage		$V_{GS}$	± 20	V	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	- 90		
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	- 52		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 100	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 160		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 50		
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	125	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	136	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	1.1	- C/W	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 40	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V	=.	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 125 °C	=.	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A	=.	0.0075	0.0094		
Dunin Course On Otata Basistanas		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 125 °C	-	-	0.0147		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 175 °C	-	-	0.0178	Ω	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 14 A	=.	0.0130	0.0160		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 17 A		=.	46	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>				5339	6675		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 20 V, f = 1 MHz	=.	852	1065	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	681	855		
Total Gate Charge <sup>c</sup>	Qg			-	103	155		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -20 \text{ V}, I_{D} = -50 \text{ A}$	=.	15	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			=.	21	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.4	2.8	4.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	13	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 20 V, $R_L$ = 0.4 $\Omega$ $I_D \cong$ - 50 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	15	23	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	61	92		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	19	29		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>				•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 160	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	I <sub>F</sub> = - 50 A, V <sub>GS</sub> = 0 V		- 0.95	- 1.5	V	

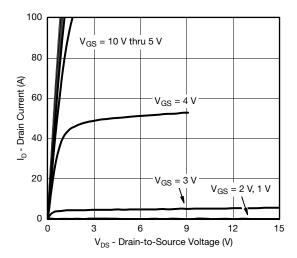
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

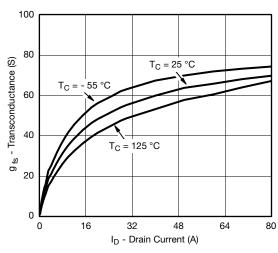
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



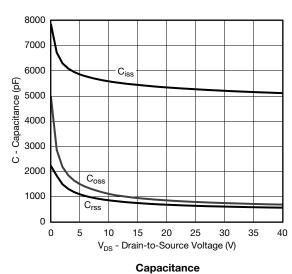
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

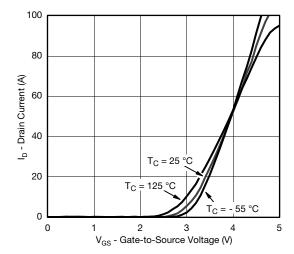


#### **Output Characteristics**

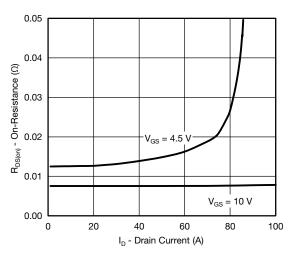


#### Transconductance

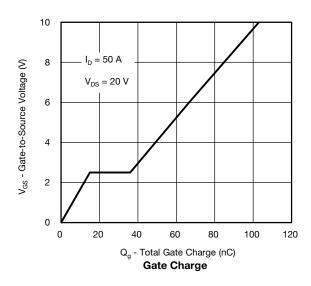




#### **Transfer Characteristics**

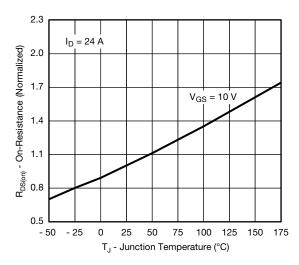


#### On-Resistance vs. Drain Current

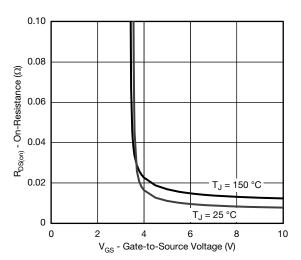




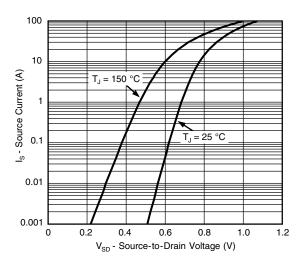
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



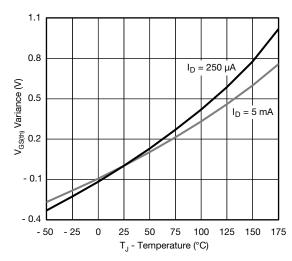
#### On-Resistance vs. Junction Temperature



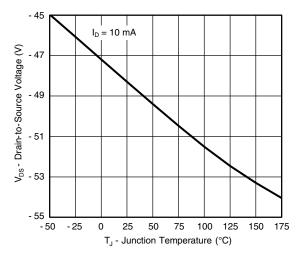
On-Resistance vs. Gate-to-Source Voltage



#### **Source Drain Diode Forward Voltage**



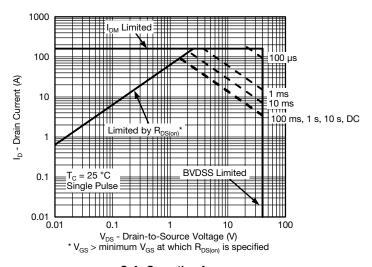
Threshold Voltage



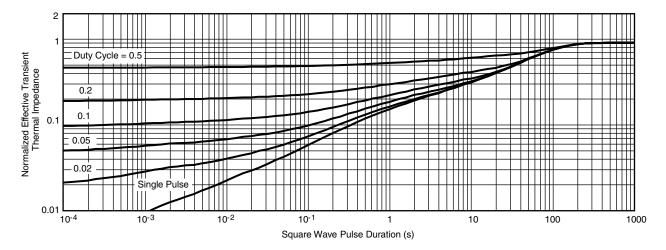
**Drain Source Breakdown vs. Junction Temperature** 



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



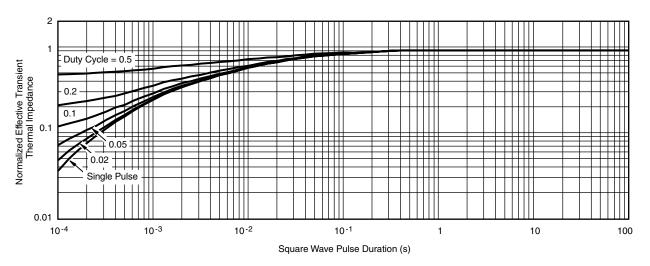
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

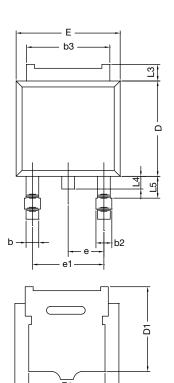
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

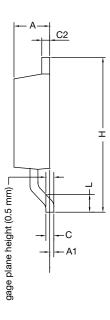
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg266743">www.vishay.com/ppg266743</a>.



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# **TO-252AA Case Outline**





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

#### DWG: 6019

Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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